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A B S T R A C T

A substrate for a transfer mask, which comprises
a first silicon layer formed of monocrystalline
silicon, a silicon oxide film formed on the first
5 silicon layer and having a thickness ranging from 0.2
to 0.8 μm , and a second silicon layer formed on the
silicon oxide film. A transfer mask which is
manufactured by making use of this substrate is
featured in that it is possible to prevent a transfer
10 pattern from being cracked or destroyed due to stress
from the silicon oxide film on the occasion of
manufacturing the transfer mask, thereby providing
a defect-free transfer mask.